

1fw

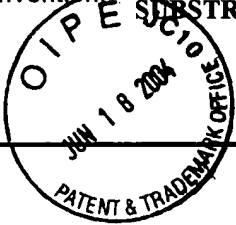
**TRANSMITTAL OF FORMAL DRAWINGS**

Docket No.  
**YOR920030586US1 (17201)**

In Re Application Of: **Tze-Chiang Chen, et al.**

Serial No.	Filing Date	Confirmation No.	Examiner	Art Unit
10/700,085	11/3/2003	Unassigned	Unassigned	2811

Invention: **METHOD FOR FABRICATING SiGe-ON-INSULATOR (SGOI) AND Ge-ON-INSULATOR (GOI) SUBSTRATES**



Address to:  
**Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450**

Transmitted herewith are:

**6** sheets of formal drawing(s) for this application.

☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).

*Signature*

**Leslie S. Szivos, Ph.D.  
Registration No. 39,394**

**Customer Number: 23389**

Dated: **June 15, 2004**

I certify that this document and attached formal drawings are being deposited on **6/15/2004** with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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**Leslie S. Szivos, Ph.D.**

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